

In the Claims:

1. (once amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,
wherein said wafer includes an area in which crystal originated particles are generated,
wherein a surface density of particles having a particle size of not less than $0.12\text{ }\mu\text{m}$ on the wafer surface is not more than 15 counts/cm^2 , even after repeating the a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing NH_4OH , H_2O_2 , and H_2O .
2. (original) A silicon single crystal wafer for a particle monitor according to Claim 1, wherein said wafer has an oxygen concentration of not more than $13 \times 10^{17}\text{ atoms/cm}^3$ (old ASTM).
3. (once amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,
wherein said wafer includes an area in which crystal originated particles are generated, and further said silicon single crystal ingot has a nitrogen concentration of $1 \times 10^{13} - 1 \times 10^{15}\text{ atoms/cm}^3$,
wherein a surface density of particles having a particle size of not less than $0.12\text{ }\mu\text{m}$ on the wafer surface is not more than 1 count/cm^2 , even after repeating the a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing NH_4OH , H_2O_2 , and H_2O .
4. (original) A silicon single crystal wafer for a particle monitor according to Claim 3, wherein said wafer has an oxygen concentration of not more than $13 \times 10^{17}\text{ atoms/cm}^3$ (old ASTM).
5. (once amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,

wherein, in said Czochralski method, the time period of passing the temperature range from 1150°C to 1070°C is within 20 min and the time period of passing the temperature range from 900°C to 800°C is within 40 min,

wherein a surface density of particles having a particle size of not less than 0.12 μm on the wafer surface is not more than 15 counts/cm², even after repeating ~~the~~ a Standard Cleaning -1,
which is made using alkaline chemical liquid mainly containing NH₄OH, H₂O₂, and H₂O.

6. (original) A silicon single crystal wafer for a particle monitor according to Claim 5, wherein said wafer has an oxygen concentration of not more than 13×10^{17} atoms/cm³ (old ASTM).

7. (once amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,

wherein, in said Czochralski method, the time period of passing the temperature range from 1150°C to 1070°C is within 20 min and the time period of passing the temperature range from 900°C to 800°C is within 40 min,

wherein said silicon single crystal ingot has a nitrogen concentration of $1 \times 10^{13} - 1 \times 10^{15}$ atoms/cm³,

wherein a surface density of particles having a particle size of not less than 0.12 μm on the wafer surface is not more than 1 count/cm², even after repeating ~~the~~ a Standard Cleaning -1, which
is made using alkaline chemical liquid mainly containing NH₄OH, H₂O₂, and H₂O.

8. (original) A silicon single crystal wafer for a particle monitor according to Claim 7, wherein said wafer has an oxygen concentration of not more than 13×10^{17} atoms/cm³ (old ASTM).

9. (once amended) A silicon single crystal wafer for a particle monitor according to ~~any one of~~ Claim 1, ~~3, 5 or 7~~, wherein, in said Standard Cleaning - 1, ~~the~~ a chemical component of ~~the~~ a used

solution is $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$, and the cleaning is repeated six times, and each cleaning is carried out for 10 min.

Please add new claims 10 – 12.

10. (new) A silicon single crystal wafer for a particle monitor according to Claim 3, wherein, in said Standard Cleaning - 1, a chemical component of a used solution is $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$, the cleaning is repeated six times, and each cleaning is carried out for 10 min.

11. (new) A silicon single crystal wafer for a particle monitor according to Claim 5, wherein, in said Standard Cleaning - 1, a chemical component of a used solution is $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$, the cleaning is repeated six times, and each cleaning is carried out for 10 min.

12. (new) A silicon single crystal wafer for a particle monitor according to Claim 7, wherein, in said Standard Cleaning - 1, a chemical component of a used solution is $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$, the cleaning is repeated six times, and each cleaning is carried out for 10 min.